

MITSUBISHI Nch POWER MOSFET

FS30KMH-06

HIGH-SPEED SWITCHING USE

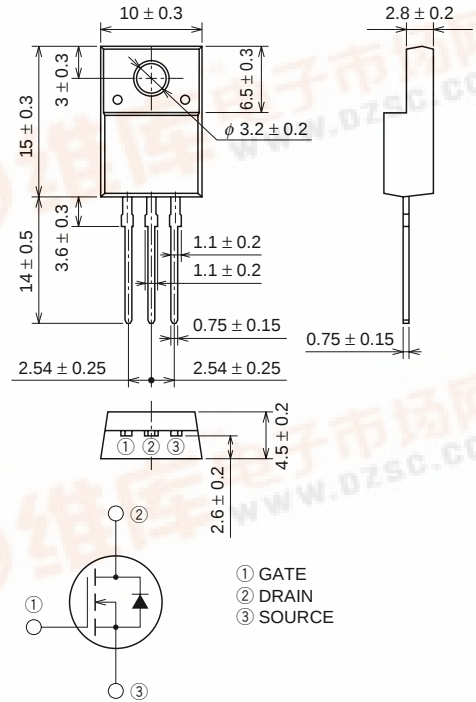
FS30KMH-06



- 2.5V DRIVE
- V_{DS} 60V
- $r_{DS(ON)}(MAX)$ 30m Ω
- I_D 30A
- Integrated Fast Recovery Diode (TYP.) 65ns
- V_{iso} 2000V

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	60	V
V_{GS}	Gate-source voltage	$V_{DS} = 0V$	±10	V
I_D	Drain current		30	A
I_{DM}	Drain current (Pulsed)		120	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	30	A
I_S	Source current		30	A
I_{SM}	Source current (Pulsed)		120	A
P_D	Maximum power dissipation		25	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
V_{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

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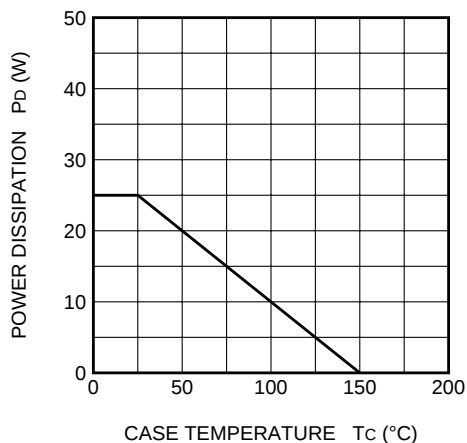
HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

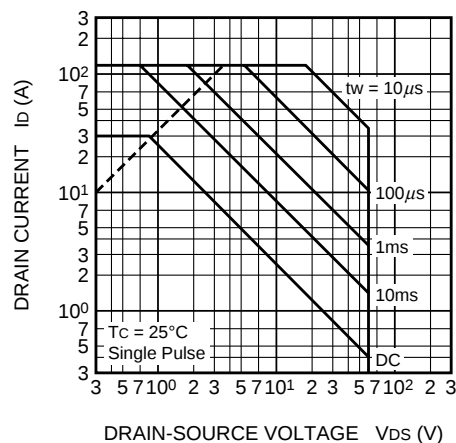
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	60	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±10V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 60V, V _{GS} = 0V	—	—	0.1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	0.6	0.9	1.2	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 15A, V _{GS} = 4V	—	25	30	mΩ
r _{DS} (ON)	Drain-source on-state resistance	I _D = 15A, V _{GS} = 2.5V	—	30	39	mΩ
V _{DS} (ON)	Drain-source on-state voltage	I _D = 15A, V _{GS} = 4V	—	0.38	0.45	V
y _{fs}	Forward transfer admittance	I _D = 15A, V _{DS} = 10V	—	34	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	2000	—	pF
C _{oss}	Output capacitance		—	320	—	pF
C _{rss}	Reverse transfer capacitance		—	170	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 30V, I _D = 15A, V _{GS} = 4V, R _{GEN} = R _{GS} = 50Ω	—	33	—	ns
t _r	Rise time		—	135	—	ns
t _d (off)	Turn-off delay time		—	145	—	ns
t _f	Fall time		—	150	—	ns
V _{SD}	Source-drain voltage	I _S = 15A, V _{GS} = 0V	—	1.0	1.5	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	5.00	°C/W
t _{rr}	Reverse recovery time	I _S = 30A, di _s /dt = -100A/μs	—	65	—	ns

PERFORMANCE CURVES

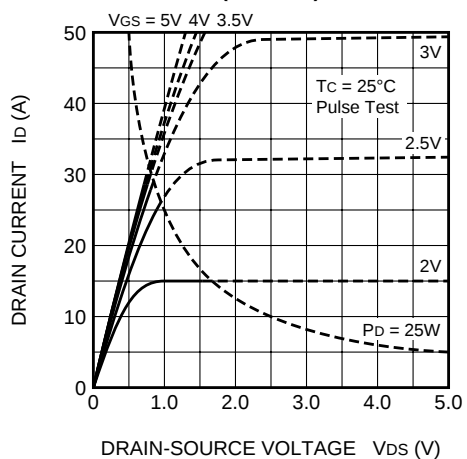
POWER DISSIPATION DERATING CURVE



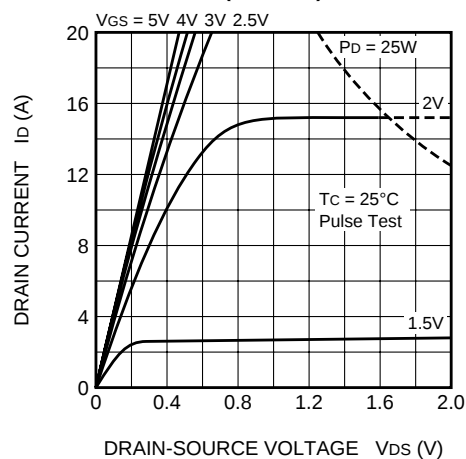
MAXIMUM SAFE OPERATING AREA



OUTPUT CHARACTERISTICS (TYPICAL)

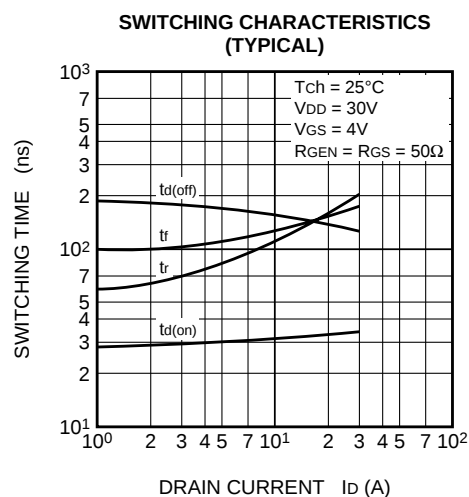
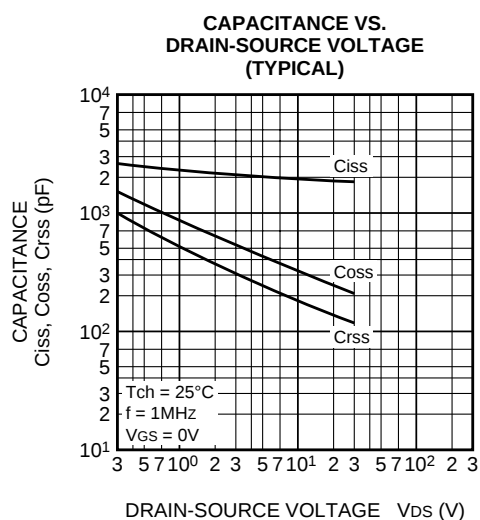
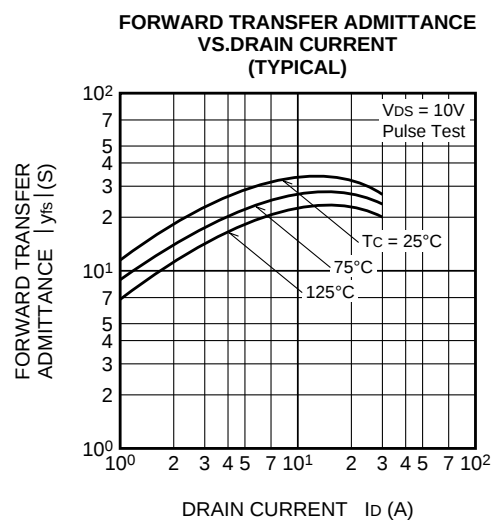
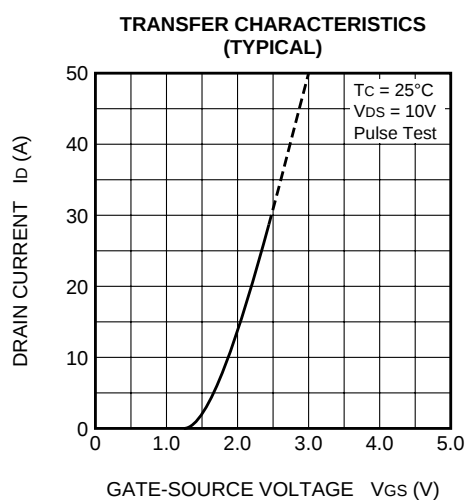
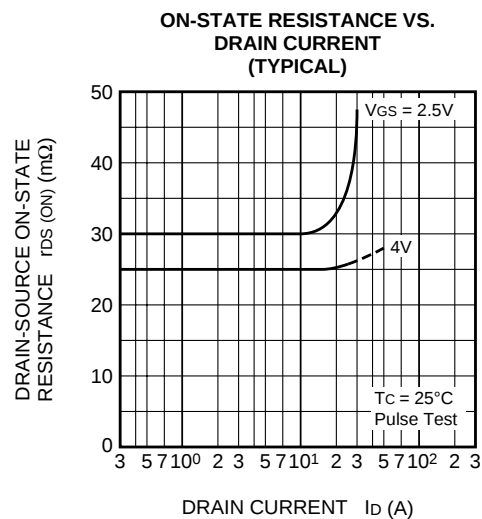
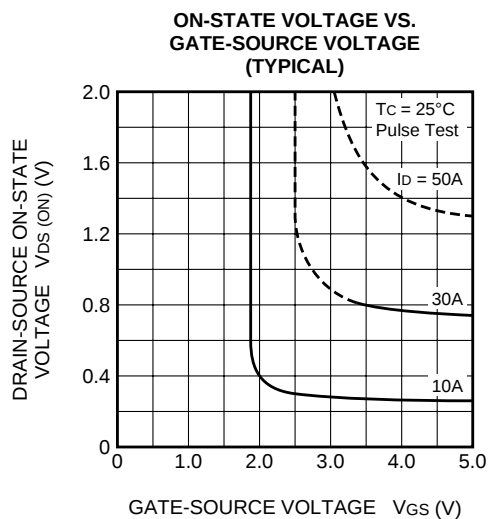


OUTPUT CHARACTERISTICS (TYPICAL)



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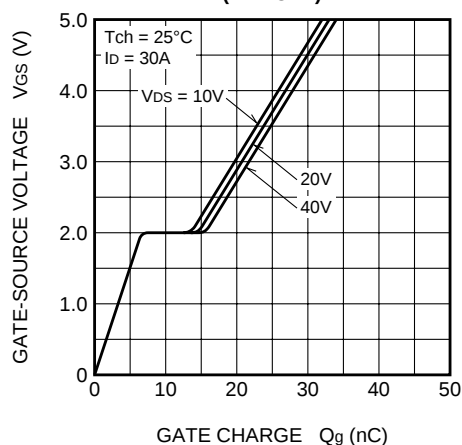
HIGH-SPEED SWITCHING USE



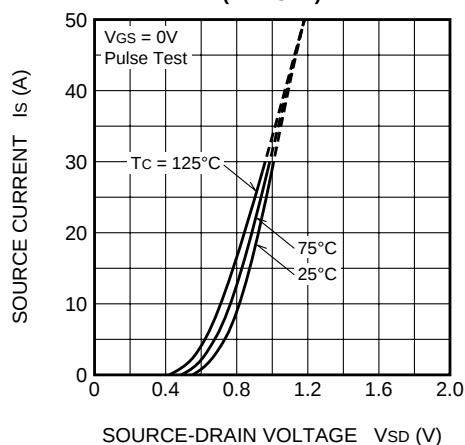
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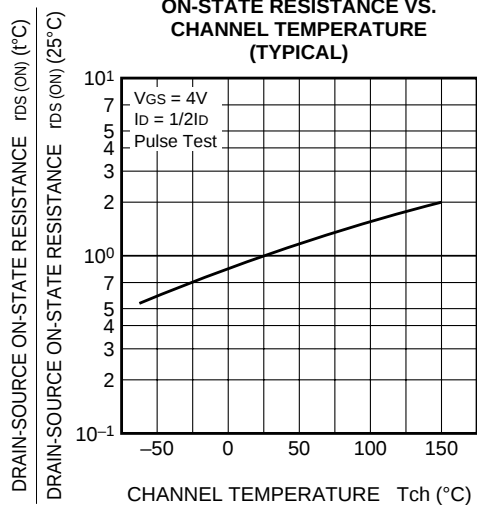
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



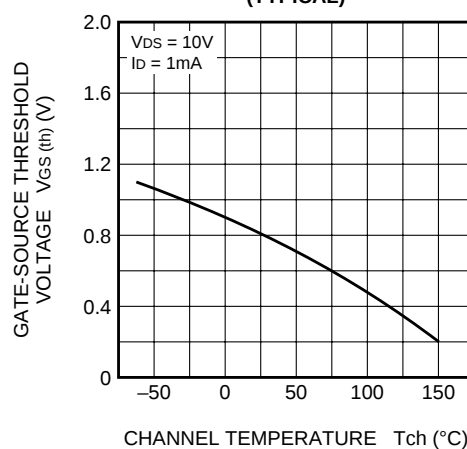
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



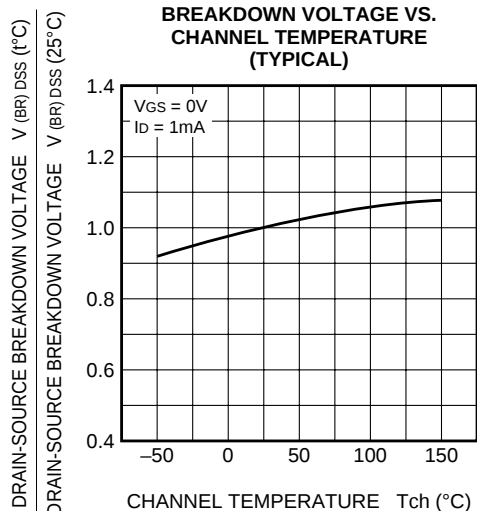
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

